

# INKA114AC1

Active Clamp  
Silicon N-channel MOSFET

## DESCRIPTION

INKA114AC1 is a Silicon N-channel Active Clamp MOSFET. The built in clamp diode connected between drain and gate protects the MOSFET from the counter electromotive force in switching drive of the inductance load. The circuit layout becomes simple because the freewheel diode is not required.

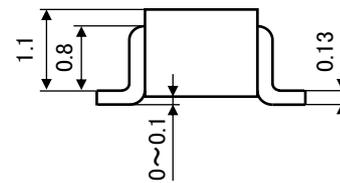
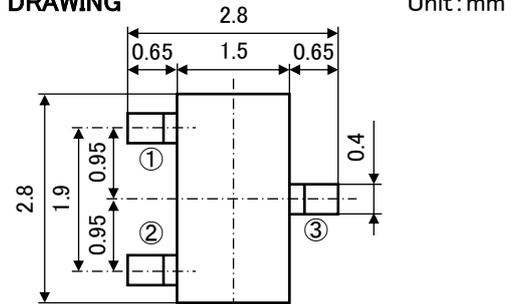
## FEATURE

- The built in clamp diode connected between drain and gate.
- Built in bias resistor enables reduction of parts count.
- Drive voltage 4V

## APPLICATION

Motor, Solenoid drive etc

## OUTLINE DRAWING



TERMINAL CONNECTOR

- ①: GATE
- ②: SOURCE
- ③: DRAIN

JEITA: SC-59

JEDEC: Similar to TO-236

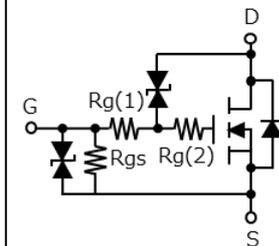
## MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Rating	Unit
Gate-Source Voltage	V <sub>GSS</sub>	10	V
Drain Current(DC) ※1	I <sub>D</sub>	0.55	A
Drain current(Pulse) ※2	I <sub>DP</sub>	1	A
Total Power Dissipation ※1	P <sub>D</sub>	400	mW
Channel Temperature	T <sub>ch</sub>	+150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

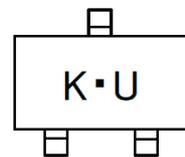
※1 package mounted on 45mm × 19mm × 1mm glass-epoxy substrate

※2 P<sub>w</sub> ≤ 1ms, Duty cycle ≤ 1%

## EQUIVALENT CIRCUIT



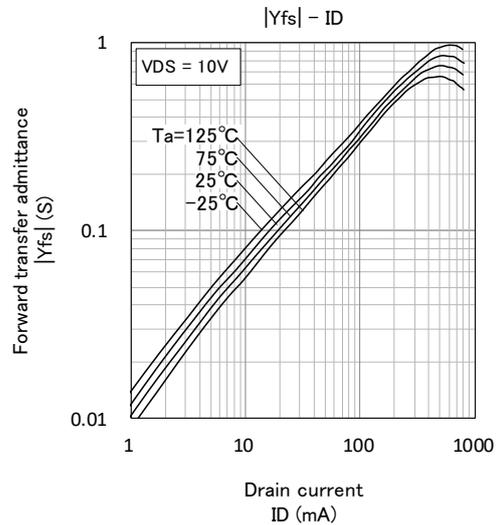
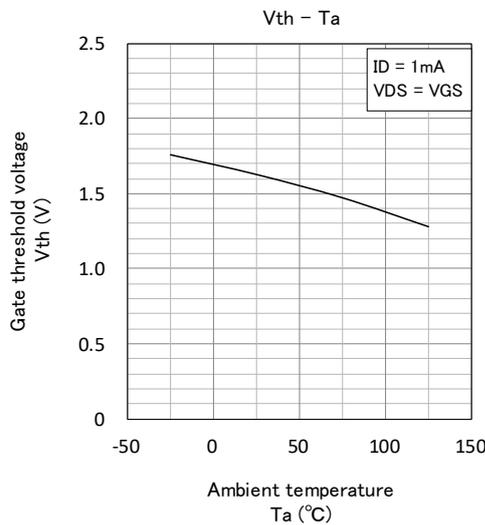
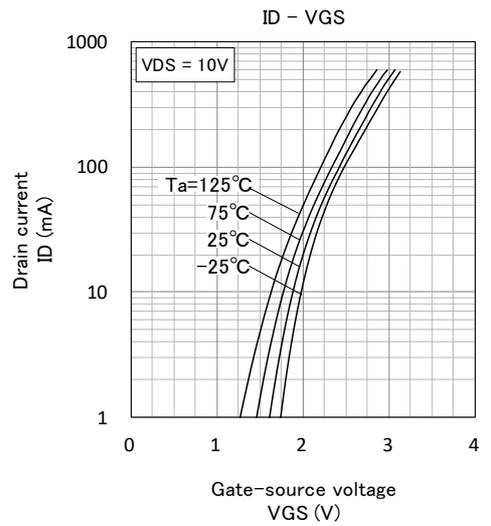
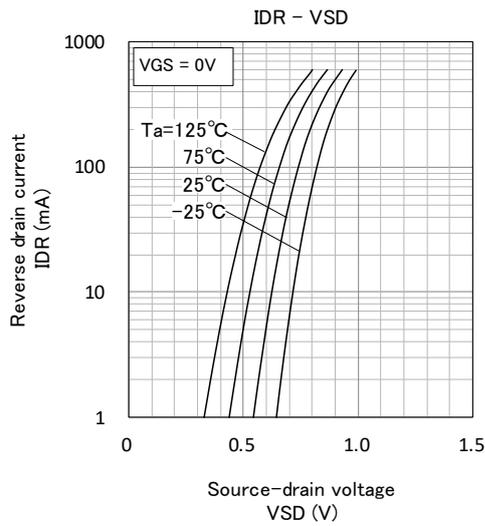
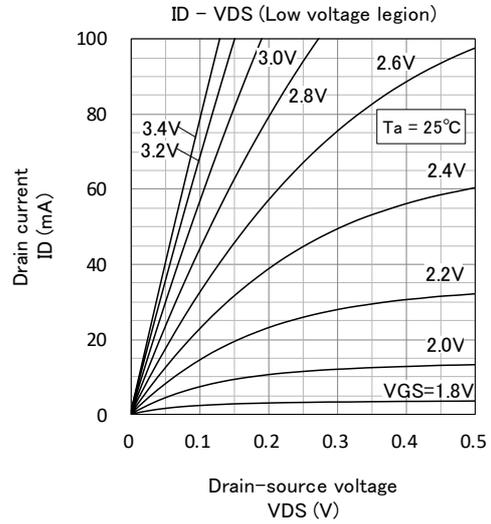
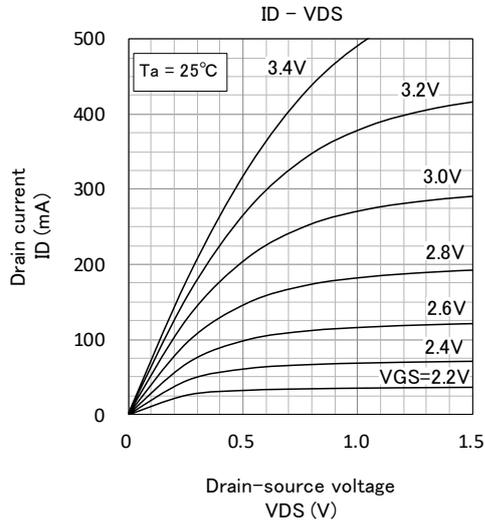
## MARKING



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

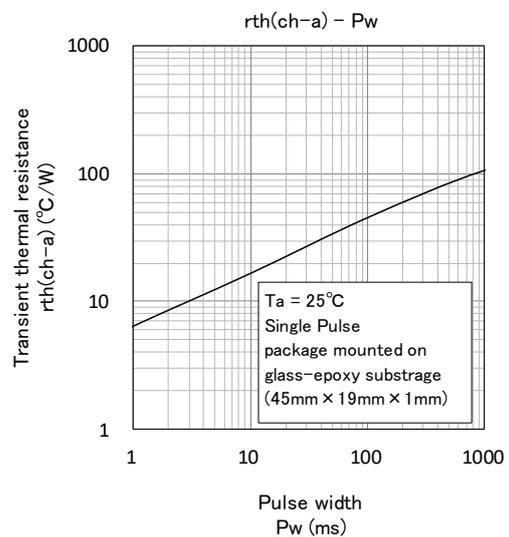
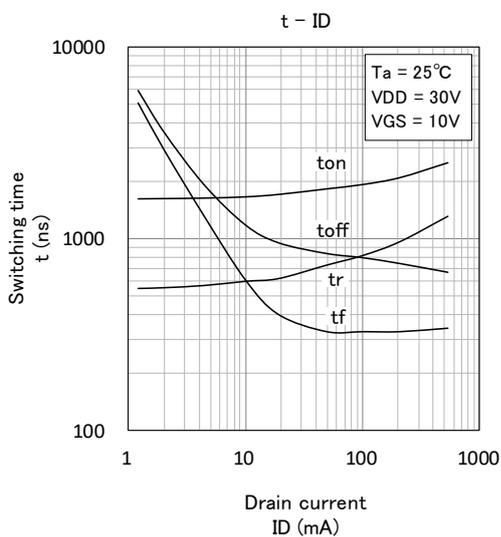
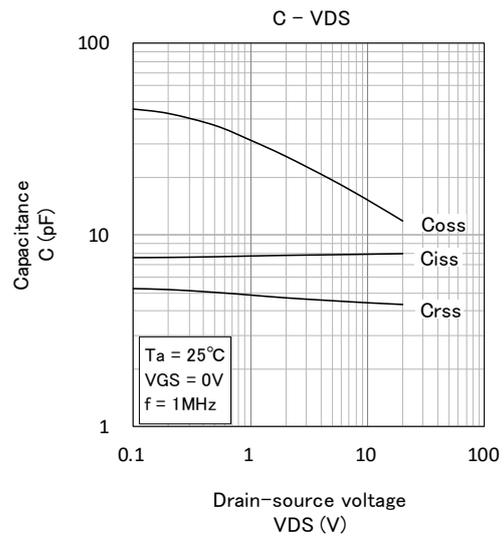
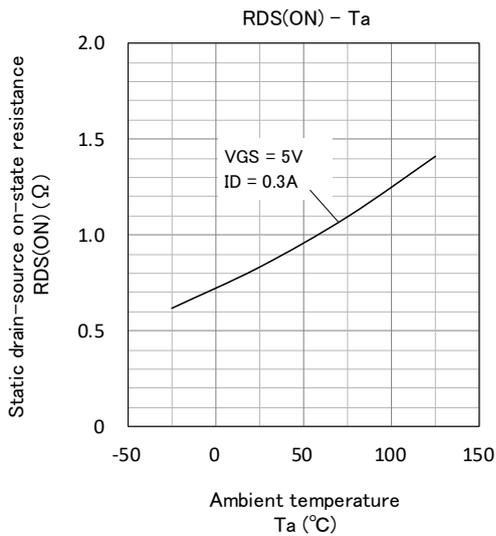
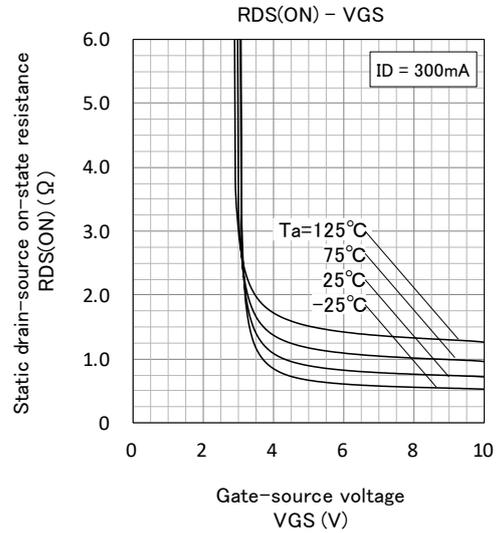
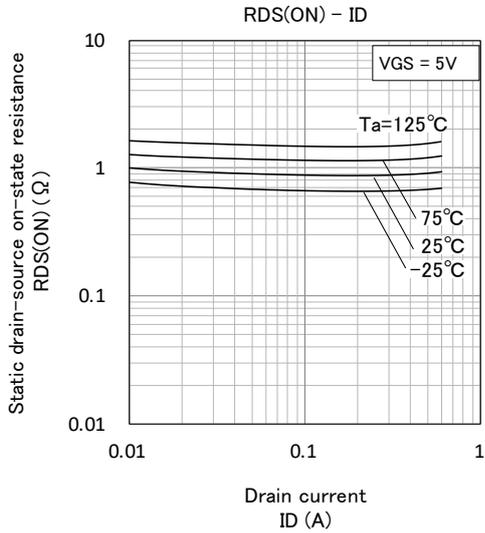
Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =10mA, V <sub>GS</sub> =0V	38	-	62	V
Gate-Source Leak current	I <sub>GSS</sub>	V <sub>GS</sub> =±5V, V <sub>DS</sub> =0V	-	-	±90	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1.0	μA
Gate Threshold Voltage	V <sub>th</sub>	I <sub>D</sub> =1mA, V <sub>DS</sub> =V <sub>GS</sub>	1.0	-	2.5	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	I <sub>D</sub> =150mA, V <sub>GS</sub> =5V	-	1.1	1.8	Ω
Gate-Source Resistance	R <sub>gs</sub>		-	100	-	kΩ
Gate Resistance1	R <sub>g1</sub>		-	10	-	kΩ
Gate Resistance2	R <sub>g2</sub>		-	500	-	Ω
Input Capacitance	C <sub>iss</sub>		-	8	-	pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz	-	16	-	pF
Feedback Capacitance	C <sub>rss</sub>		-	5	-	pF
Switching Time	t <sub>on</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =100mA	-	2.1	-	μs
	t <sub>off</sub>	V <sub>GS</sub> =0~10V	-	0.9	-	μs

## TYPICAL CHARACTERISTICS



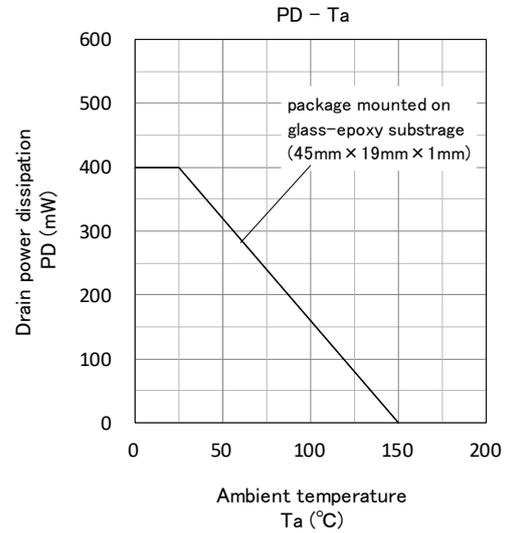
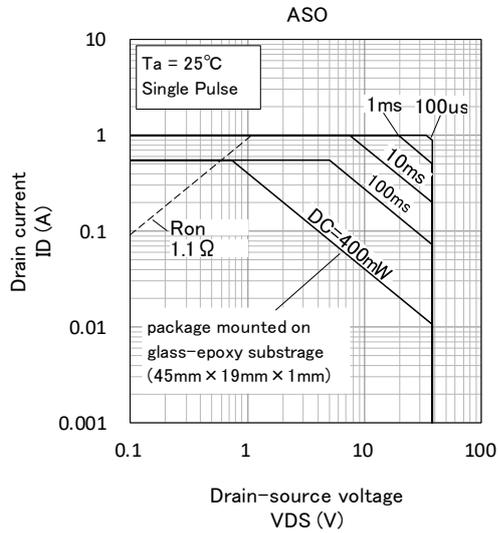
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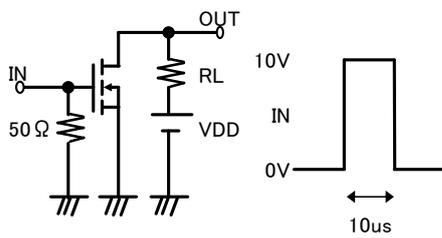


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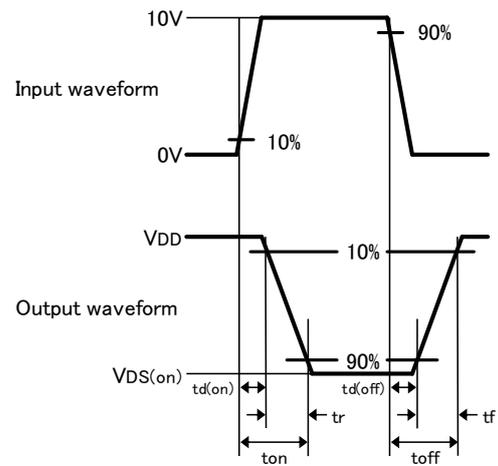
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## Switching time test condition



Duty  $\leq 1\%$   
Input:  $t_r, t_f < 10\text{ns}$   
VDD = 30V  
Common source  
 $T_a = 25^\circ\text{C}$



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**Keep safety first in your circuit designs!**

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